Gate-tunable band-edge in few-layer MoS_2

Michele Masseroni,^{1,*} Isaac Soltero,^{2,3,*} James G. McHugh,^{2,3} Igor Rozhansky,^{2,3}

Xue Li,^{2,3} Alexander Schmidhuber,¹ Markus Niese,¹ Takashi Taniguchi,⁴ Kenji Watanabe,⁵ Vladimir I. Fal'ko,^{2,3} Thomas Ihn,^{1,6} and Klaus Ensslin^{1,6},[†]

¹Solid State Physics Laboratory, ETH Zürich, 8093 Zürich, Switzerland

²Department of Physics and Astronomy, University of Manchester,

Oxford Road, Manchester, M13 9PL, United Kingdom

³National Graphene Institute, University of Manchester,

Booth St. E., Manchester, M13 9PL, United Kingdom

⁴Research Center for Materials Nanoarchitectonics,

National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-0044, Japan

⁵Research Center for Electronic and Optical Materials,

National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-0044. Japan

⁶Quantum Center, ETH Zürich, 8093 Zürich, Switzerland

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Transition metal dichalcogenides (TMDs) have garnered significant research interest due to the variation in band-edge locations within the hexagonal Brillouin zone between single-layer and bulk configurations. In monolayers, the conduction band minima are centered at the K-points, whereas in multilayers, they shift to the Q-points, midway between the Γ and K points. In this study, we conduct magnetotransport experiments to measure the occupation in the Q and K valleys in fourlayer molybdenum disulfide (MoS₂). We demonstrate electrostatic tunability of the conduction band edge by combining our experimental results with a hybrid $k \cdot p$ tight-binding model that accounts for interlayer screening effects in a self-consistent manner. Furthermore, we extend our model to bilayer and trilayer MoS_2 , reconciling prior experimental results and quantifying the tunable range of band edges in atomically thin TMDs.

INTRODUCTION I.

Transition metal dichalcogenides (TMDs) display unique electronic [1-3] and optical properties [4, 5]. A key feature of TMDs is the presence of multiple valleys in their band structure, with the conduction band hosting valleys at both the K points and the Q points (located midway between the Γ and K points) of the first Brillouin zone, while the valence band exhibits valleys at the K points and the Γ point [6]. The relative energy levels of these valleys are strongly influenced by the number of layers, leading to layer-dependent modifications in the band structure [7, 8].

In our previous studies, we systematically investigated the conduction band of single layer [9], bilayer [10], and trilayer MoS_2 [11]. We found that electron transport predominantly occurred via the K valleys of the conduction band, while the occupation of Q valleys, predicted by theory [12–17], was not detected in our measurements. In these studies, we employed electrostatic gating to overcome the Schottky barrier that typically forms at the metal-MoS₂ interface. However, the influence of the gateinduced electric field on the band structure, particularly the relative energy shift of different valleys [18], was not considered.

Here, we investigate four-layer MoS_2 , where we observe a gate-dependent band edge transition in the conduction

band minima, shifting from the Q valleys at low gate voltages to the K valleys at higher voltages. This transition reveals the sensitivity of the conduction band to external electric fields, which we attribute to the differing atomic orbital compositions of the Q and K valleys, as well as interlayer screening effects. Our findings not only demonstrate the coexistence of both Q and K valleys in biased four-layer MoS_2 , but also show how electrostatic gating can effectively tune the band structure in TMDbased devices. These results offer deeper insights into the electronic properties of multilayer MoS_2 and present potential avenues for valley-selective device applications.

II. RESULTS AND DISCUSSION

In this study, we use dual-gated, multi-terminal devices, as shown in Fig. 1(a). The devices are heterostructures consisting of four-layer MoS_2 encapsulated in hexagonal boron nitride (hBN), all obtained by mechanical exfoliation. We conducted the experiments on two samples: Sample A, featuring a graphite bottom gate and a metallic top gate, and Sample B, with metallic gates on both sides. The results presented in the main text are from Sample A, which exhibits higher electron mobility and more pronounced Shubnikov-de Haas oscillations (SdHO). Similar results obtained in Sample B are provided in the Supplementary Information.

One of the challenges of electronic transport experiments in MoS_2 devices is achieving ohmic contacts. This issue is effectively addressed by employing a sample ge-

^{*} These authors contributed equally to this work.

[†] Contact author: ensslin@phys.ethz.ch



Figure 1. (a) Schematic view (left panel) and optical image of the sample (right panel). In the right panel, the MoS₂ layer is outlined with a black dashed line. The gate defines a conducting channel of width $W = 2 \,\mu\text{m}$. The distance between adjacent contacts is $L_{\rm C-C} = 3 \,\mu\text{m}$. (b) Four-terminal resistivity (blue) and mobility (black) as a function of the bottom gate voltage at $V_{\rm TG} = 12 \,\text{V}$. The vertical dashed line mark the voltage at which additional bands are populated. This measurement was performed at a temperature of $T \approx 100 \,\text{mK}$.

ometry with gated metallic contacts [2, 9, 19–21]. In such samples, finite conductance at cryogenic temperatures is achieved only at relatively large top gate voltages ($V_{\rm TG}$), which are required to overcome the Schottky barrier at the metal-MoS₂ interface.

For this reason, in our experiments, we fix the top gate voltage and tune the density with the bottom gate voltage (V_{BG}), which does not affect the electron density in the region of the contacts due to the screening provided by the metallic contact pads. This enables us to maintain low-resistive (~ 1 k Ω) ohmic contacts for all densities in the Hall bar. However, this sample geometry restricts the parameter space spanned by the gates. As a consequence, the samples are typically operated under finite electric displacement field (D), which affects the electron distribution across layers in multilayer MoS₂, potentially affecting their electronic properties.

In Fig. 1(b), we present the resistivity (blue) as a function of $V_{\rm BG}$ measured at $V_{\rm TG} = 12$ V and a temperature of $T \approx 100$ mK. The resistivity reveals a non-monotonic dependence on $V_{\rm BG}$, which is also evident in the transport mobility (black). The mobility increases

roughly linearly in the voltage range $V_{\rm BG} < -1.7 \,\rm V$ (regime A in the figure), reaching a peak value of $\mu_{\rm peak} \approx 1.5 \times 10^4 \,\rm cm^2$, $(\rm Vs)^{-1}$ at an electron density of approximately $1 \times 10^{13} \,\rm cm^{-2}$. Further increasing $V_{\rm BG}$ results in a significant drop in mobility, which we attribute to the population of a second band, similar to our observation in three layer MoS₂ samples [11].

To investigate the contribution of the different bands in four-layer MoS₂, we examine the data obtained at finite magnetic fields. In Fig. 2(a), we present the magnetoresistance $\Delta \rho_{xx}/\rho_0 = [\rho_{xx}(B) - \rho_{xx}(0)]/\rho_{xx}(0)$ as a function of $V_{\rm BG}$ measured at $V_{\rm TG} = 12$ V. This measurement reveals an intricate pattern that originates from overlapping Landau fans. The observation of multiple Landau fans confirm the existence of multiple electronic bands.

Each of those bands has a corresponding electron density which determines the frequency of the SdHO. We extract the densities by computing the Fast Fourier Transform (FFT) of $\Delta \rho_{xx}(B^{-1})$ (see details in the Supplementary Information) and plot the resulting densities in Fig. 2(b). In the voltage range $V_{\rm BG} < -1.7 \,\rm V$ (regime A), the Fourier analysis reveals two electron densities, $n_{K,1}$ and $n_{K,2}$ (blue and green curves), both with a similar gate voltage dependence. The densities are calculated using the relationship $n_i = g_i e f_i / h$, where f_i is the frequency, g_i is the degeneracy of band i, e is the elementary charge and h is Plank's constant. By comparing the sum $n_{K,1} + n_{K,2}$ (gray curve) to the total density $n_{\rm H}$ obtained from the Hall effect measurements (red curve), we determine a degeneracy of g = 2 for both bands. This degeneracy suggests that the bands are centered at the K points of the Brillouin zone.

The density difference $n_{K,1} - n_{K,2}$ arises from the spinorbit splitting of the K valley. By linear extrapolation, we estimate $n_{K,1} \approx 3.2 \times 10^{12} \text{ cm}^{-2}$ at the onset of the density $n_{K,2}$, which aligns with the density required to populate the upper spin-orbit split band at the K points observed in previous studies in monolayer [9], bilayer [10], and three-layer [11] MoS₂. This further supports our interpretation.

Now, we turn our attention to regime B in Fig.2(b), where an additional band starts getting populated. This is evident in three distinct aspects. The first is the emergence of another Landau fan in Fig.2(a) (highlighted by the white dashed frame), with its origin around $V_{BG} \approx$ -1.7 V. At the same gate voltage, the Hall density exhibits a plateau (marked by an arrow), which we attribute to the filling of defect states at the bottom of the newly occupied band. This results in the localization of electrons at the defects, preventing them from contributing to the Hall effect (see also the Supplementary Information for further discussion). Thirdly, the sum $n_{K,1} + n_{K,2}$ is no longer equal to the Hall density implying the presence of an extra electron pocket.

We determine the degeneracy of the newly occupied band by calculating the residual density using the relation $n_{\rm res} = n_{\rm tot} - n_{K,1} - n_{K,2}$ [depicted by the pink curve in Fig. 2(b)] and using it to predict the Landau fan ac-



Figure 2. (a) $\Delta \rho_{xx}/\rho_0 = [\rho_{xx}(B) - \rho_{xx}(0)]/\rho_{xx}(0)$ plotted as a function of $V_{\rm BG}$ and B at $V_{\rm TG} = 12$ V and $T \approx 100$ mK. The white dashed frame highlight the zoom-in displayed in panel(c). (b) Electron densities as a function of $V_{\rm BG}$. The total density (n_{tot}) is shown by the black dashed line, Hall density $(n_{\rm H})$ is represented by the red solid line, and the densities obtained from the SdHO frequencies $(n_{K,i} = 2ef_{K,i}/h)$ with i = 1, 2) by the blue and green solid lines. The residual density $(n_{\rm res} = n_{\rm tot} - n_{K,1} - n_{K,2})$ is shown by the pink solid line. The schematic on the right shows the hexagonal Brillouin zone of MoS_2 , with the electron in the K and Q valleys depicted by the colored pockets. (c) Zoom-in of panel (a), showing the Landau fan (pink solid lines) expected for the residual density, accounting for a degeneracy of g = 12. The dashed horizontal lines in regime C highlight the saturation of the densities in the K and Q valleys.

cording to the equation

$$B_m(V_{\rm BG}) = \frac{hn_{\rm res}(V_{\rm BG})}{e\,g\,m},\tag{1}$$

where *m* is an integer representing the Landau level index, and *g* is the band degeneracy. In Fig. 2(c), we plot the calculated Landau fan, where we match the minima of $\Delta \rho_{xx}/\rho_0$ by assuming g = 12. This large degeneracy suggests that the residual electron density originates from the *Q* valley, which has a sixfold valley degeneracy. To achieve a total degeneracy of 12, the bands must be spin degenerate, implying inversion symmetry. However, while inversion symmetry is preserved in unbiased MoS₂ samples with an even number of layers, the large displacement field in regime B ($D \sim 1 \text{V/nm}$) is expected to break this symmetry.

To gain further insight, we implement a model to analyze the layer-resolved valley densities in four-layer MoS₂ under various displacement fields and total electron densities. This model incorporates self-consistent screening effects produced by charge accumulation in each layer, allowing us to capture the impact of inter-layer screening on the electron distribution. We construct hybrid $k \cdot p$ tight-binding Hamiltonians to simulate the electronic structure of the K and Q valleys. These Hamiltonians were initially parametrized using density functional theory (DFT) calculations (see Supplementary Information) and included an on-site term to account for electrostatic band bending due to external fields. Notably, DFT results confirmed the absence of hybridization between the K valleys of different layers, consistent with prior results [10]. According to the findings in Ref. [22], the spin-orbit splitting between K bands, Δ_{SO}^{K} , and the monolayer energy offset between K and Q valleys, E_{KQ} , undergoes significant renormalization due to electron-electron exchange interactions. In line with this framework, we considered both of these quantities as layer-density dependent (see Supplementary Information).

The predictive accuracy of the model is based on two essential parameters: t_0 , the inter-layer tunnel coupling for Q valleys, and E_{KQ} . However, DFT-derived parameters exhibit a pronounced sensitivity to subtle variations in the MoS_2 interlayer spacing and lattice constants. This sensitivity introduces considerable uncertainty in their precise values, and, in fact, theoretical values alone did not align with our experimental results. To overcome this limitation, we varied t_0 and E_{KQ} semi-empirically to achieve a better fit to the observed layer and valley densities. Remarkably, we found that the distribution of electron densities across layers and valleys is highly sensitive to variations in t_0 and E_{KQ} . This characteristic suggests a novel experimental approach for determining inter-layer tunnel coupling, which may also be extended to other TMDs. The optimized parameters for four-layer MoS_2 determined through this process are $t_0 = 0.16 \text{ eV}$ and $E_{KQ} = 0.21 \, \text{eV}.$

The band densities obtained from our model are shown in Fig. 3(a) as a function of V_{BG} for $V_{TG} = 12$ V, allowing a direct comparison with the experimental densities in Fig. 2(b). The model identifies three distinct operating regimes controlled by the bottom gate voltage, reflecting the experimental observations. In regime A, where the voltage is applied asymmetrically between the top and bottom gates, the density is concentrated entirely in the K valleys of the top layer [see the layer polarization shown in Fig. 3(b)]. In regime B, where the bottom gate voltage is close to zero, the Q valleys begin to fill with electrons, and charge is transferred from the K valley to the newly occupied band. Since the Q valley states are hybridized between layers, the density is distributed across layers, favoring layers with lower potential energy. In regime C, the K valleys in the bottom layers are filled, leading to the saturation of the K (top layer) and Q valley densities, as observed in the experiment.

This model successfully captures the gate voltage dependence of the valley-specific densities and provide insights into the layer distribution of electron densities. In regime B, the model predicts an asymmetric density distribution across the layers, which results in a spin degeneracy lifting of Q valley states when $D \neq 0$, due to SOC [see dotted lines in Fig. 3(a)]. This prediction aligns with a detailed analysis of the FFT spectrum (see Supplementary Information), where we observe a splitting of the SdHO frequency corresponding to the residual density.

The experimentally observed splitting of the Q valley is notably less pronounced than predicted by our model. This discrepancy may arise from crystal field effects at the interface with the hBN dielectrics [23]. In the Supplementary Information, we account for the influence of hBN by introducing an on-site potential energy difference, $\Delta_{\rm hBN}$, between the outer layers (which interface directly with hBN) and the inner layers. Incorporating this offset reduces the hybridization between the Q vallevs of the outer and inner layers. This adjustment results in a more symmetric layer distribution of the Qvalley electrons, thereby mitigating inversion symmetry breaking induced by the displacement field and leading to a weaker spin-orbit splitting. Consequently, the model's prediction of spin-orbit splitting becomes more consistent with the experimental observations.

Next, we examine the effect of the top gate voltage, focusing on the densities in the Q and K valley of the top layer. To track the top gate dependence of these densities, we present the FFT of $\Delta \rho_{xx}(B^{-1})$ at $V_{\rm BG} = 3.5 \,\rm V$ for various $V_{\rm TG}$ in Fig. 4(a). In this regime, the finite $V_{\rm BG}$ allows us to observe oscillations originating from both Qand K valley states of the top layer without inducing charges in the K valleys of the bottom layer. Figure 4(b) shows that the K valley frequency of the top layer increases with $V_{\rm TG}$, while the Q valley frequency is nearly constant due to interlayer screening. These data suggest that the top gate voltage induces a transition of the band edge from the Q valleys at low gate voltages to the K valleys at higher voltages.

In Fig. 4(c), we compare valley densities predicted



Figure 3. (a) Band densities obtained from the theoretical model using the parameters $E_{QK} = 0.21 \,\text{eV}$ and $t_0 = 0.16 \,\text{eV}$. The densities are plotted as a function of V_{BG} at $V_{TG} = 12 \text{ V}$, enabling a direct comparison with Fig. 2(b). The densities in the K valleys of the top layer (layer 1), $n_{K,1,t}$ and $n_{K,2,t}$, are shown as solid blue and green lines, respectively. The K valley densities in the bottom layer (layer 4) are depicted with dashed lines following the same color code. The total density in the Q valleys $(n_{Q,1} + n_{Q,2}$ for a direct comparison with the experiment) is represented by the pink solid line, while the individual components are shown by the dotted lines. (b) The three panels show the percentage of the total density distributed across the four MoS₂ layers with the different bands encoded by the colors [consistent with panel (a)]. As a representation of the three regimes we selected specific gate voltage configurations: $(V_{\rm TG} = 12 \, {\rm V}, V_{\rm BG} = -6 \, {\rm V})$ for regime A, $(V_{\rm TG} = 12 \, {\rm V}, V_{\rm BG} = 0 \, {\rm V})$ regime B, and $(V_{\rm TG} = 12 \,\mathrm{V}, V_{\rm BG} = 8 \,\mathrm{V})$ for regime C.

by the model (solid lines) with experimental densities (square markers), showing a good agreement. Due to high contact resistance, the low $V_{\rm TG}$ regime is experimentally inaccessible, so we rely on model predictions for this range. According to the model, at low bias ($V_{\rm TG} < 4.5 \,\rm V$), the Q valley remains the only occupied band, confirming that the conduction band minimum in low-biased four-layer MoS₂ is located at the Q point and demonstrating the presence of a gate-induced Q-K band edge transition.

Having established the relevance of the gate bias in determining the relative band alignment in multilayer MoS_2 , we extended our model to bilayer and three-layer systems (see Supplementary Information) to address



Figure 4. (a) FFT of $\Delta \rho_{xx}(B^{-1})$ at $V_{\rm BG} = 3.5$ V and various $V_{\rm TG}$. The peaks associated to the Q and K_1 valleys are highlighted by the vertical pink and blue line, respectively. (b) The frequencies obtained from panel (a) plotted as a function of $V_{\rm TG}$. (c) Comparison between the densities obtained from the model (solid lines) and the densities obtained from the experiment (square markers). The model parameters are the same of Fig. 3

discrepancies between experiments and DFT-calculated band structures. Using consistent model parameters, $E_{\rm KQ} = 0.21 \,\text{eV}$ and $t_0 = 0.16 \,\text{eV}$, we successfully reproduce the experimental findings across multiple layers.

For biased bilayer MoS_2 , the model predicts that the K valleys in top and bottom layers are occupied bands, while the Q valleys are not, as observed in Ref. [10]. In our earlier study on three-layer MoS_2 [11], we observed electron transport predominantly through the K valleys in the outer layers, although the band contributing to the electrons in the middle layer remained unidentified. Our model reveals the missing element in our previous work, showing that both K and Q valleys were populated, as observed in the four-layer case.

III. CONCLUSION

In conclusion, our study provides a comprehensive understanding of the gate-tunable band structure and valley occupation in four-layer MoS_2 through a combination of magnetotransport experiments and a self-consistent hybrid $k \cdot p$ tight-binding model. At low gate voltages, we confirm that the conduction band minimum is centered at the Q point, in line with theoretical expectations for multilayer MoS_2 . However, as the gate voltage increases, charge redistribution towards the layer closest to the positive gate electrode induces a transition of the band edge from the Q valleys to the K valleys. By extending our model to bilayer and three-layer MoS_2 , we successfully bridge previous discrepancies between experimental observations [10, 11] and density functional theory predictions [12–17], underscoring the importance of interlayer screening and layer-specific charge accumulation in determining valley occupation. These findings highlight the intricate interplay between the K and Q valleys in multilayer MoS_2 , paving the way for future valleytronic and electronic applications that exploit layer-specific charge and valley control.

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AUTHOR CONTRIBUTIONS

M.M., T.I., K.E. conceived and designed the experiments. M.M. fabricated the device with inputs from T.I. and K.E.. M.M., performed the measurements with inputs from T.I and K.E.. M.M. and A.S. analyzed the experimental data with inputs from M.N., T.I., and K.E.. I.S. and V.F. developed the theoretical model with inputs from J.G.M., I.R., and X.L.. M.M. designed the figures with inputs from I.S.. T.T., K.W. supplied the hexagonal boron nitride. M.M wrote the manuscript with inputs from I.S., J.G.M. and I.R.. All the coauthors mentioned above read and commented on the manuscript. M.M. and I.S. contributed equally to this work.